

SEPP9.001APC

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

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9/5/01
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Applicant : Leskela et al.) Group Art Unit Unknown
Intl. Appl. No. : PCT/FI99/00741)
Intl. Filed : September 13, 1999)
For : METHOD FOR GROWING)
OXIDE THIN FILMS)
CONTAINING BARIUM AND)
STRONTIUM)
Examiner : Unknown)

PRELIMINARY AMENDMENT

Assistant Commissioner for Patents
Washington, D.C. 20231

Dear Sir:

Preliminary to examination on the merits, please amend the above-captioned U.S. national phase application as follows:

IN THE SPECIFICATION:

On page 1 of the Specification, after the Title of the Invention ending on line 1 and before the sentence on line 4 which begins, "The present invention..." please insert: This is the U.S. national phase under 35 U.S.C. § 371 of International Application PCT/FI99/00741, filed September 13, 1999.

IN THE CLAIMS:

Please amend the claims as follows:

1. (Amended) A method for growing oxide thin films on a substrate in a reactor, comprising producing the films by the Atomic Layer Epitaxy (ALE) process by feeding pulses of precursor compounds into the reactor, wherein the precursor compounds comprise:
at least one cyclopentadienyl compound of strontium and/or barium;